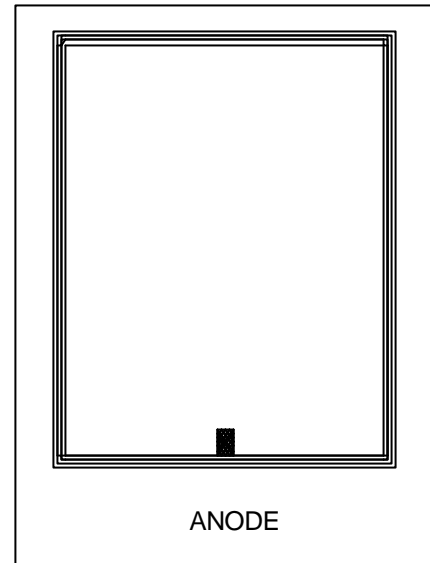


QSD-1300

SILICON PHOTODIODE

COMMON CATHODE TYPE PHOTO DIODE.
HIGH EFFICIENCY SENSITIVITY.

- **DIE SIZE** 3.00mm × 3.00mm
- **DIE THICKNESS** 400 ± 15μm
- **METALLIZATION**
 - TOP Al
 - BOTTOM Au
- **PASSIVATION** Silicon Nitride
- **BONDING PAD SIZE**
 - ANODE(TOP) 160μm × 160μm
 - CATHODE(BOTTOM)



• ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)

Parameter	Symbol	Maximum rating	Unit
Reverse Breakdown Voltage	B _{VR}	35	V
Junction Temperature	T _J	150	°C

• ELECTRICAL / OPTICAL CHARACTERISTICS (Ta= 25° C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Open Circuit Voltage	V _{OP}	Note(1)	0.3	0.4		V
Short Circuit Current	I _{SC}	Note(1)	70	87		μA
Junction Capacitance	C _J	V=3V, f=1MHz		30	50	pF
Spectrum Sensitivity	λ		450 ~ 1,100			nm
Peak Sensing Wavelength	λ _P			940		nm
Forward Voltage	V _F	I _F =100 mA			1.5	V
Dark Current	I _D	V _R =10V			10	nA
Reverse Breakdown Voltage	B _{VR}	I _R =10μA	50	80		V

Note(1): Parallel light of 1,000 Lux illumination is applied by a Tungsten lamp of 2856k.